

Final datasheet

EasyPIM™ module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode and NTC

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{ nom}} = 25\text{ A} / I_{CRM} = 50\text{ A}$
 - Overload operation up to 175°C
 - Low $V_{CE,\text{sat}}$
 - TRENCHSTOP™ IGBT7
 - Suitable Infineon gate drivers can be found under <https://www.infineon.com/gdfinder>
- Mechanical features
 - Solder contact technology
 - 2.5 kV AC 1 minute insulation
 - Al_2O_3 substrate with low thermal resistance
 - Compact design
 - High power density



Typical appearance

Potential applications

- Auxiliary inverters
- Motor drives
- Air conditioning

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

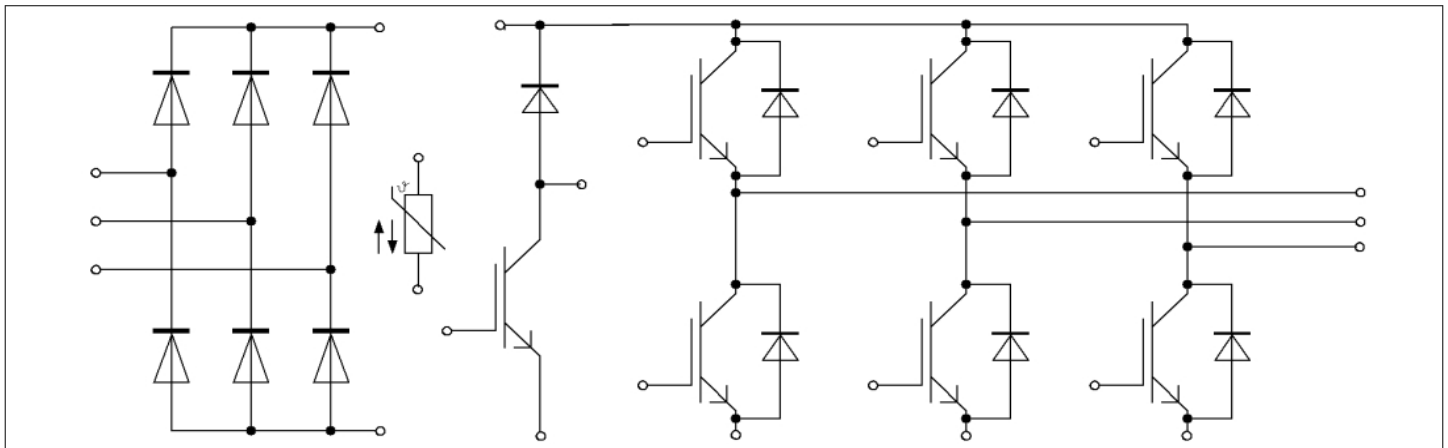


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50$ Hz, $t = 1$ min	2.5	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Comparative tracking index	CTI		> 200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{SCE}			30		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_H = 25$ °C, per switch		6		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_H = 25$ °C, per switch		8		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting force per clamp	F		20		50	N
Weight	G			24		g

Note: The current under continuous operation is limited to 30A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25$ °C	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj\ max} = 175$ °C $T_H = 105$ °C	25	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\ op}$	50	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 25\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.60	1.85	V
			$T_{vj} = 125\ ^\circ C$		1.74		
			$T_{vj} = 175\ ^\circ C$		1.82		
Gate threshold voltage	V_{GETh}	$I_C = 0.525\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.15	5.8	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CC} = 600\ V, T_{vj} = 25\ ^\circ C$			0.395		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			0.0		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			4.77		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.017		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			0.0056	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 25\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 6.2\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.037		μs
			$T_{vj} = 125\ ^\circ C$		0.039		
			$T_{vj} = 175\ ^\circ C$		0.040		
Rise time (inductive load)	t_r	$I_C = 25\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 6.2\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.020		μs
			$T_{vj} = 125\ ^\circ C$		0.024		
			$T_{vj} = 175\ ^\circ C$		0.025		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 25\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 6.2\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.186		μs
			$T_{vj} = 125\ ^\circ C$		0.291		
			$T_{vj} = 175\ ^\circ C$		0.334		
Fall time (inductive load)	t_f	$I_C = 25\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 6.2\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.173		μs
			$T_{vj} = 125\ ^\circ C$		0.220		
			$T_{vj} = 175\ ^\circ C$		0.285		
Turn-on energy loss per pulse	E_{on}	$I_C = 25\ A, V_{CC} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 6.2\ \Omega, di/dt = 950\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		1.55		mJ
			$T_{vj} = 125\ ^\circ C$		2.1		
			$T_{vj} = 175\ ^\circ C$		2.45		
Turn-off energy loss per pulse	E_{off}	$I_C = 25\ A, V_{CC} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 6.2\ \Omega, dv/dt = 2900\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		1.58		mJ
			$T_{vj} = 125\ ^\circ C$		2.45		
			$T_{vj} = 175\ ^\circ C$		3.05		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
SC data	I_{SC}	$V_{GE} \leq 15 \text{ V}, V_{CC} = 800 \text{ V}, V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_p \leq 8 \mu\text{s}, T_{vj} = 150 \text{ }^\circ\text{C}$		80		A
			$t_p \leq 7 \mu\text{s}, T_{vj} = 175 \text{ }^\circ\text{C}$		75		
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT, $\lambda_{grease} = 4.3 \text{ W}/(\text{m}\cdot\text{K})$		1.30		K/W	
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	$^\circ\text{C}$	

Note: $T_{vj\text{ op}} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25 \text{ }^\circ\text{C}$	1200	V	
Continuous DC forward current	I_F		25	A	
Repetitive peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$	50	A	
I^2t - value	I^2t	$t_p = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ }^\circ\text{C}$	72.5	A^2s
			$T_{vj} = 175 \text{ }^\circ\text{C}$	63	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	V_F	$I_F = 25 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1.83	2.30	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.70		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		1.63		
Peak reverse recovery current	I_{RM}	$V_{CC} = 600 \text{ V}, I_F = 25 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 950 \text{ A}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		24.2		A
			$T_{vj} = 125 \text{ }^\circ\text{C}$		32.4		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		37.6		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Recovered charge	Q_r	$V_{CC} = 600\text{ V}, I_F = 25\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 950\text{ A}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$		2.25	μC
			$T_{vj} = 125\text{ }^\circ\text{C}$		3.82	
			$T_{vj} = 175\text{ }^\circ\text{C}$		4.95	
Reverse recovery energy	E_{rec}	$V_{CC} = 600\text{ V}, I_F = 25\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 950\text{ A}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$		0.65	mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$		1.41	
			$T_{vj} = 175\text{ }^\circ\text{C}$		1.87	
Thermal resistance, junction to heat sink	R_{thJH}	per diode, $\lambda_{grease} = 4.3\text{ W}/(\text{m}\cdot\text{K})$			1.96	K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	$^\circ\text{C}$

Note: $T_{vj\text{ op}} > 150\text{ }^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 Diode, Rectifier

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\text{ }^\circ\text{C}$	1600	V	
Maximum RMS forward current per chip	I_{FRMSM}	$T_H = 100\text{ }^\circ\text{C}$	25	A	
Maximum RMS current at rectifier output	I_{RMSM}	$T_H = 100\text{ }^\circ\text{C}$	25	A	
Surge forward current	I_{FSM}	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ }^\circ\text{C}$	300	A
			$T_{vj} = 150\text{ }^\circ\text{C}$	245	
I^2t - value	I^2t	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ }^\circ\text{C}$	450	A^2s
			$T_{vj} = 150\text{ }^\circ\text{C}$	300	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 10\text{ A}, T_{vj} = 150\text{ }^\circ\text{C}$		0.80		V
Reverse current	I_r	$T_{vj} = 150\text{ }^\circ\text{C}, V_R = 1600\text{ V}$		1		mA
Thermal resistance, junction to heat sink	R_{thJH}	per diode, $\lambda_{grease} = 4.3\text{ W}/(\text{m}\cdot\text{K})$		1.50		K/W

(table continues...)

Table 8 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Temperature under switching conditions	$T_{vj,op}$		-40		150	°C

5 IGBT, Brake-Chopper

Table 9 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25\text{ °C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj,max} = 175\text{ °C}$ $T_H = 105\text{ °C}$	25	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj,op}$	50	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE,sat}$	$I_C = 25\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$	1.60	1.85	V
			$T_{vj} = 125\text{ °C}$	1.74		
			$T_{vj} = 175\text{ °C}$	1.82		
Gate threshold voltage	V_{GETh}	$I_C = 0.525\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25\text{ °C}$	5.15	5.8	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\text{ V}, V_{CC} = 600\text{ V}, T_{vj} = 25\text{ °C}$		0.395		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\text{ °C}$		0.0		Ω
Input capacitance	C_{ies}	$f = 100\text{ kHz}, T_{vj} = 25\text{ °C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		4.77		nF
Reverse transfer capacitance	C_{res}	$f = 100\text{ kHz}, T_{vj} = 25\text{ °C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		0.017		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}$ $T_{vj} = 25\text{ °C}$			0.0056	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25\text{ °C}$			100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 25\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 10\text{ Ω}$	$T_{vj} = 25\text{ °C}$	0.058		μs
			$T_{vj} = 125\text{ °C}$	0.060		
			$T_{vj} = 175\text{ °C}$	0.061		

(table continues...)

Table 10 (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rise time (inductive load)	t_r	$I_C = 25 \text{ A}, V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Gon} = 10 \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}$	0.055		μs
			$T_{vj} = 125 \text{ }^\circ\text{C}$	0.057		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	0.058		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 25 \text{ A}, V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Goff} = 10 \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}$	0.205		μs
			$T_{vj} = 125 \text{ }^\circ\text{C}$	0.310		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	0.353		
Fall time (inductive load)	t_f	$I_C = 25 \text{ A}, V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Goff} = 10 \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}$	0.173		μs
			$T_{vj} = 125 \text{ }^\circ\text{C}$	0.220		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	0.285		
Turn-on energy loss per pulse	E_{on}	$I_C = 25 \text{ A}, V_{CC} = 600 \text{ V}, L_\sigma = 35 \text{ nH}, V_{GE} = \pm 15 \text{ V}, R_{Gon} = 10 \Omega, di/dt = 320 \text{ A}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$	2.15		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$	2.65		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	2.9		
Turn-off energy loss per pulse	E_{off}	$I_C = 25 \text{ A}, V_{CC} = 600 \text{ V}, L_\sigma = 35 \text{ nH}, V_{GE} = \pm 15 \text{ V}, R_{Goff} = 10 \Omega, dv/dt = 2900 \text{ V}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$	1.58		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$	2.45		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	3.05		
SC data	I_{SC}	$V_{GE} \leq 15 \text{ V}, V_{CC} = 800 \text{ V}, V_{CEmax} = V_{CES} - L_{sCE} * di/dt$	$t_p \leq 8 \mu\text{s}, T_{vj} = 150 \text{ }^\circ\text{C}$	80		A
			$t_p \leq 7 \mu\text{s}, T_{vj} = 175 \text{ }^\circ\text{C}$	75		
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT, $\lambda_{grease} = 4.3 \text{ W}/(\text{m}\cdot\text{K})$		1.27		K/W
Temperature under switching conditions	$T_{vj op}$		-40		175	$^\circ\text{C}$

Note: $T_{vj op} > 150 \text{ }^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

6 Diode, Brake-Chopper

Table 11 **Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25 \text{ }^\circ\text{C}$	1200	V
Continuous DC forward current	I_F		10	A

(table continues...)

Table 11 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$	20	A	
I^2t - value	I^2t	$t_p = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ }^\circ\text{C}$	27.5	A^2s
			$T_{vj} = 175 \text{ }^\circ\text{C}$	24	

Table 12 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	V_F	$I_F = 10 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1.72	2.10	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.59		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		1.52		
Peak reverse recovery current	I_{RM}	$V_{CC} = 600 \text{ V}, I_F = 10 \text{ A}, -di_F/dt = 300 \text{ A}/\mu\text{s}$ ($T_{vj} = 175 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		8.1		A
			$T_{vj} = 125 \text{ }^\circ\text{C}$		10.1		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		11.7		
Recovered charge	Q_r	$V_{CC} = 600 \text{ V}, I_F = 10 \text{ A}, -di_F/dt = 300 \text{ A}/\mu\text{s}$ ($T_{vj} = 175 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		0.74		μC
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.37		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		1.84		
Reverse recovery energy	E_{rec}	$V_{CC} = 600 \text{ V}, I_F = 10 \text{ A}, -di_F/dt = 300 \text{ A}/\mu\text{s}$ ($T_{vj} = 175 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		0.26		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$		0.52		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		0.72		
Thermal resistance, junction to heat sink	R_{thJH}	per diode, $\lambda_{grease} = 4.3 \text{ W}/(\text{m}\cdot\text{K})$		2.96		K/W	
Temperature under switching conditions	T_{vjop}		-40		175	$^\circ\text{C}$	

Note: $T_{vjop} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

7 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25 \text{ }^\circ\text{C}$		5		k Ω
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100 \text{ }^\circ\text{C}, R_{100} = 493 \text{ } \Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25 \text{ }^\circ\text{C}$			20	mW

(table continues...)

Table 13 (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

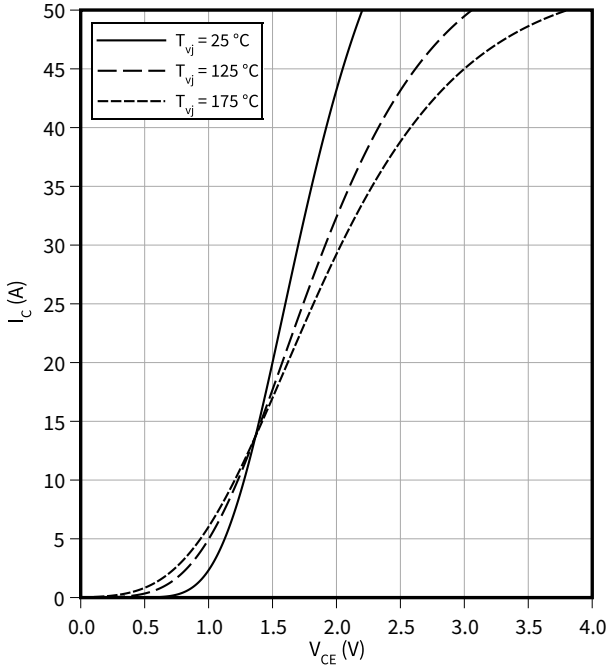
Note: For an analytical description of the NTC characteristics please refer to AN2009-10, chapter 4

8 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

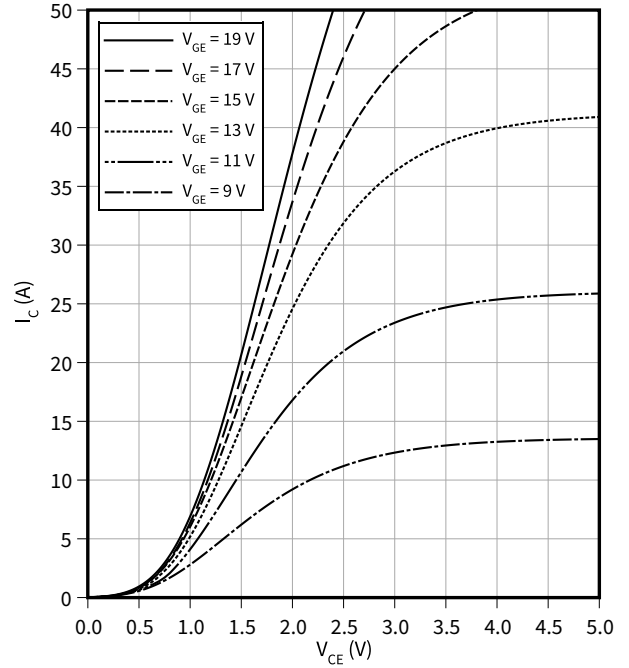
$$V_{GE} = 15 \text{ V}$$



Output characteristic field (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

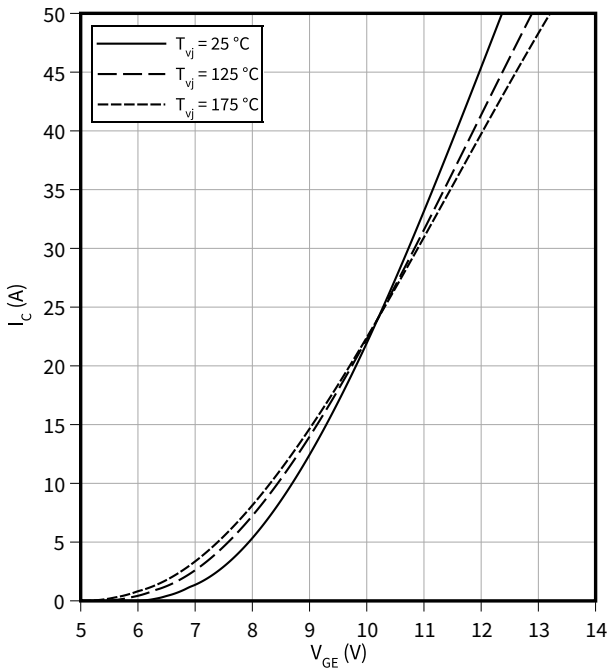
$$T_{vj} = 175 \text{ °C}$$



Transfer characteristic (typical), IGBT, Inverter

$$I_C = f(V_{GE})$$

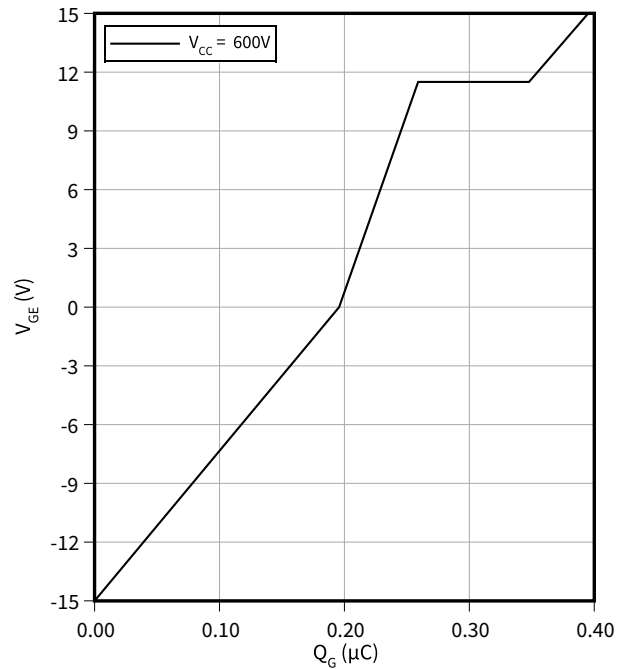
$$V_{CE} = 20 \text{ V}$$



Gate charge characteristic (typical), IGBT, Inverter

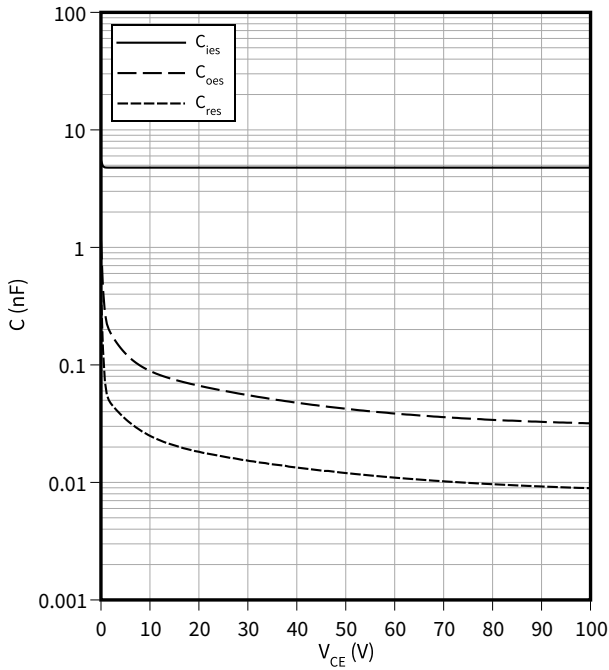
$$V_{GE} = f(Q_G)$$

$$T_{vj} = 25 \text{ °C}, I_C = 25 \text{ A}$$



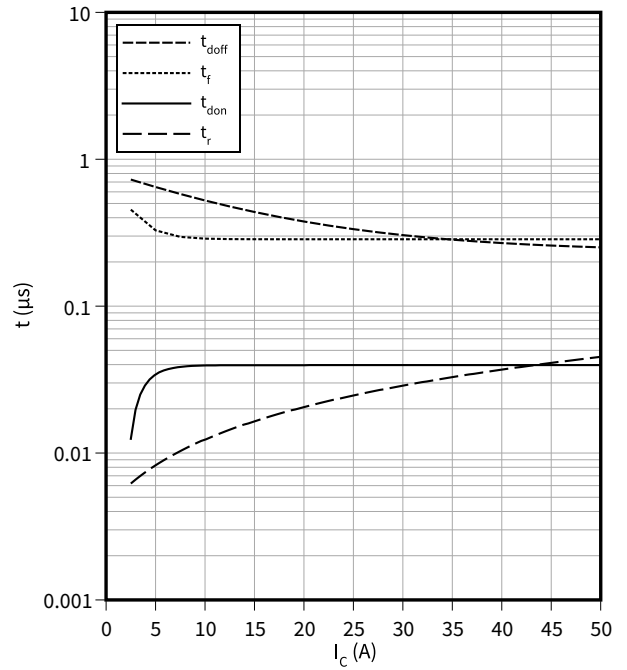
Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$
 $f = 100 \text{ kHz}, T_{vj} = 25 \text{ }^\circ\text{C}, V_{GE} = 0 \text{ V}$



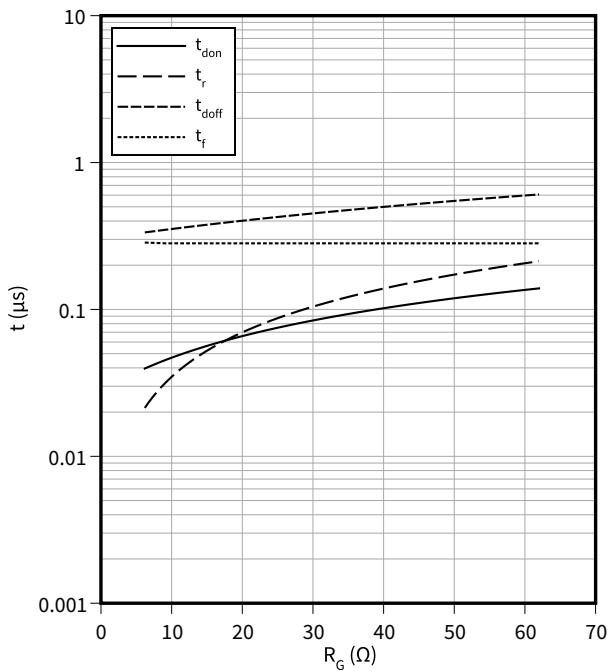
Switching times (typical), IGBT, Inverter

$t = f(I_C)$
 $R_{Goff} = 6.2 \text{ } \Omega, R_{Gon} = 6.2 \text{ } \Omega, V_{GE} = \pm 15 \text{ V}, V_{CC} = 600 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}$



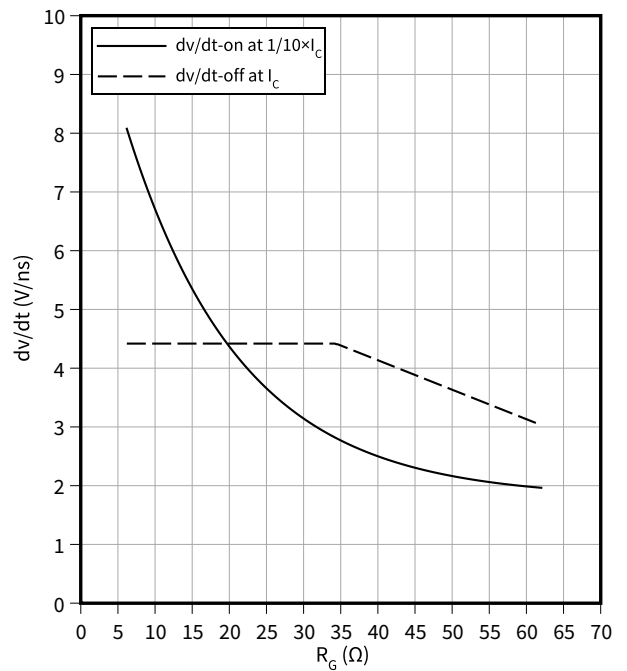
Switching times (typical), IGBT, Inverter

$t = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}, I_C = 25 \text{ A}, V_{CC} = 600 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}$



Voltage slope (typical), IGBT, Inverter

$dv/dt = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}, I_C = 25 \text{ A}, V_{CC} = 600 \text{ V}, T_{vj} = 25 \text{ }^\circ\text{C}$

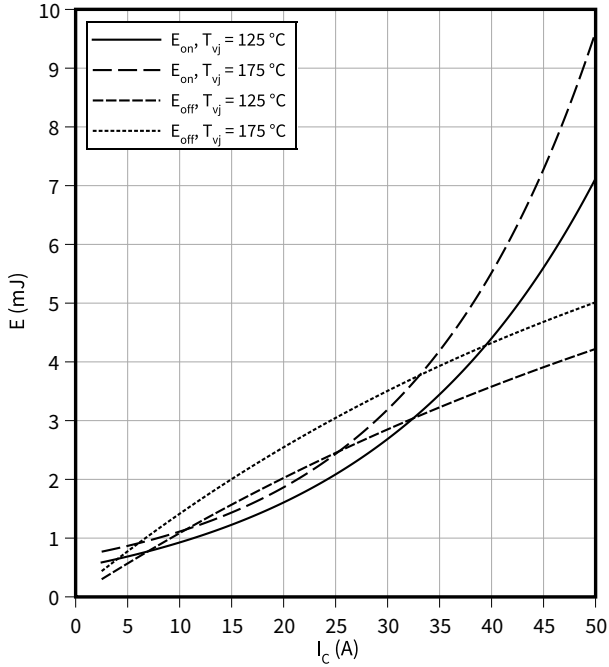


8 Characteristics diagrams

Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

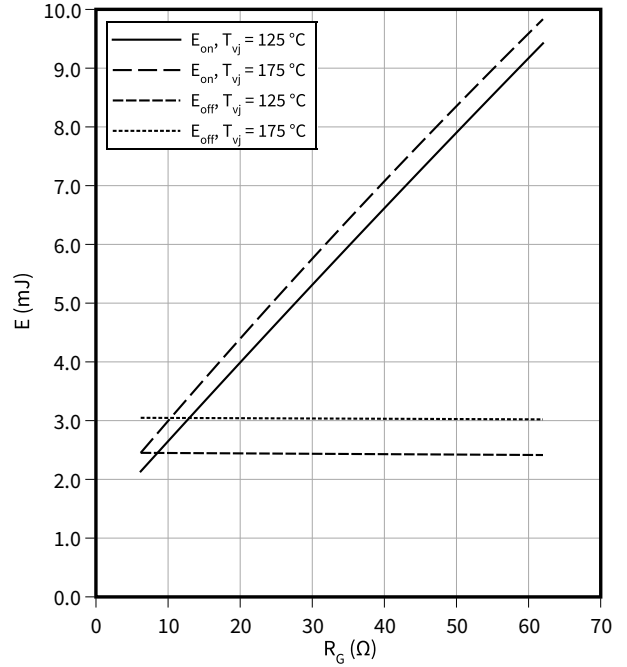
$R_{Goff} = 6.2 \Omega, R_{Gon} = 6.2 \Omega, V_{GE} = \pm 15 V, V_{CC} = 600 V$



Switching losses (typical), IGBT, Inverter

$E = f(R_G)$

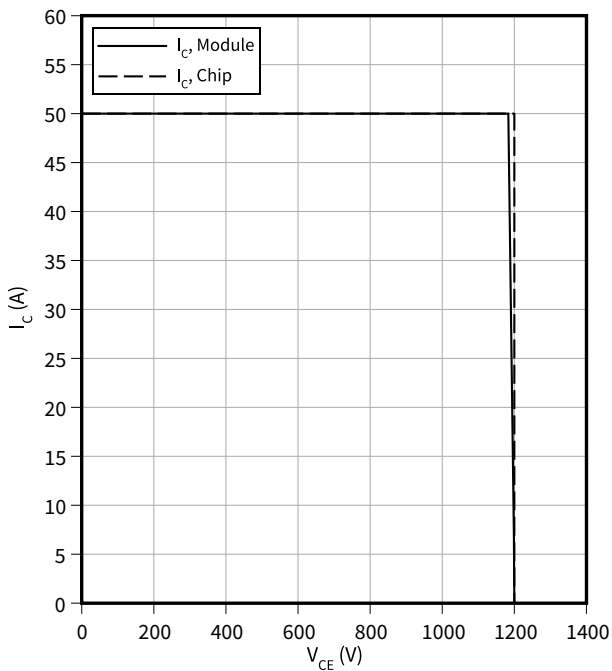
$V_{GE} = \pm 15 V, I_C = 25 A, V_{CC} = 600 V$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

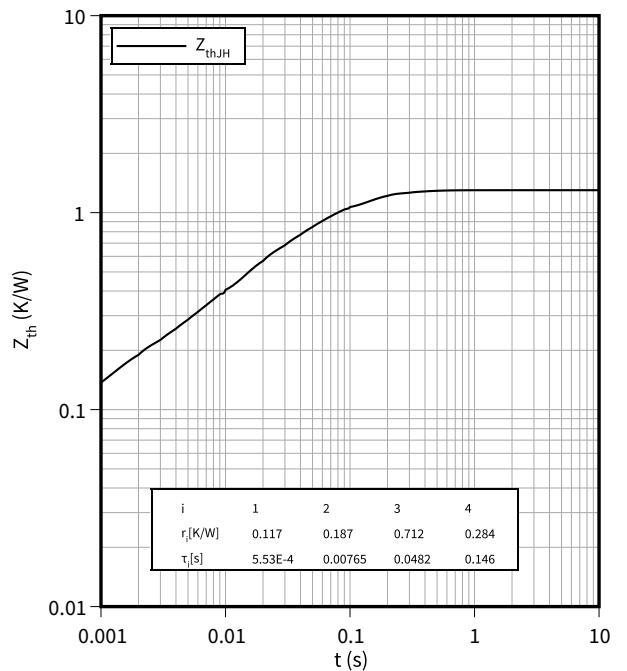
$I_C = f(V_{CE})$

$R_{Goff} = 6.2 \Omega, V_{GE} = \pm 15 V, T_{vj} = 175 \text{ °C}$



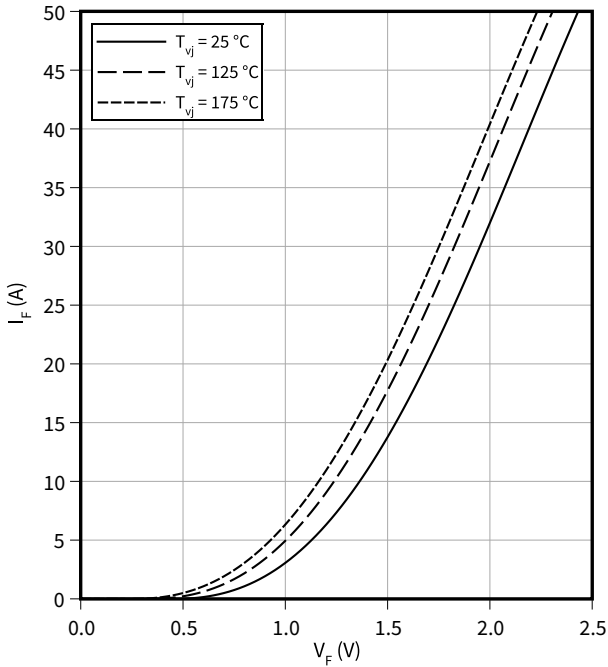
Transient thermal impedance, IGBT, Inverter

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, Inverter

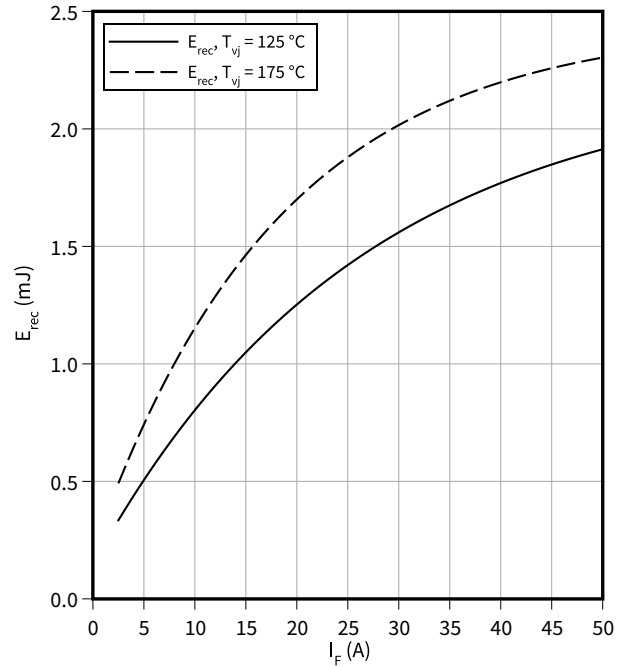
$I_F = f(V_F)$



Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

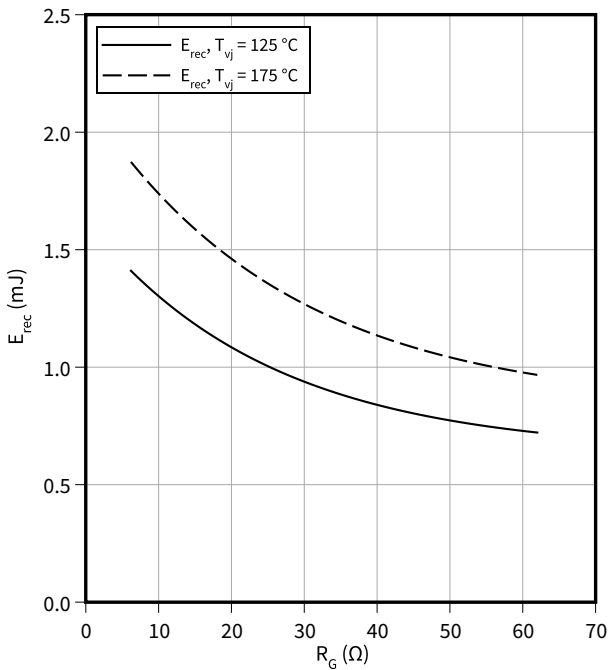
$R_{Gon} = 6.2 \Omega, V_{CC} = 600 \text{ V}$



Switching losses (typical), Diode, Inverter

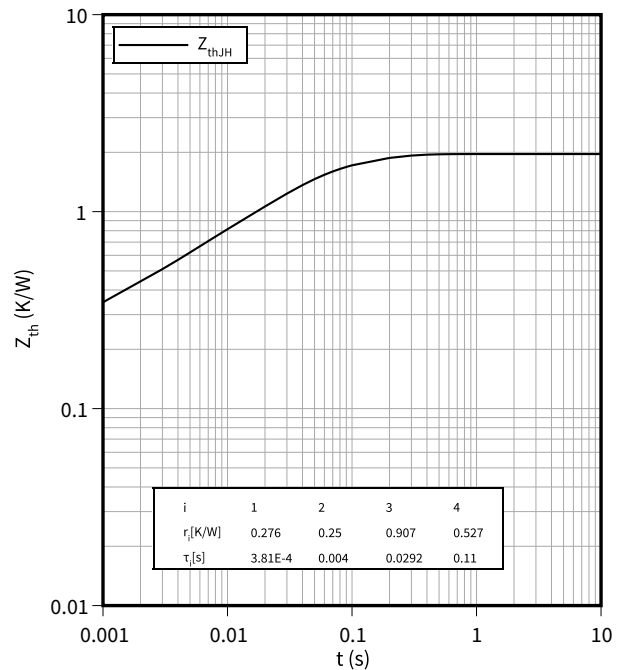
$E_{rec} = f(R_G)$

$I_F = 25 \text{ A}, V_{CC} = 600 \text{ V}$



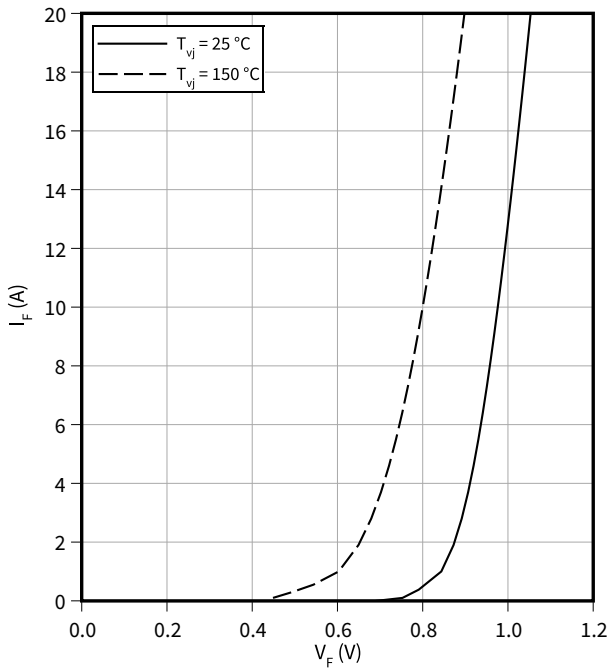
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



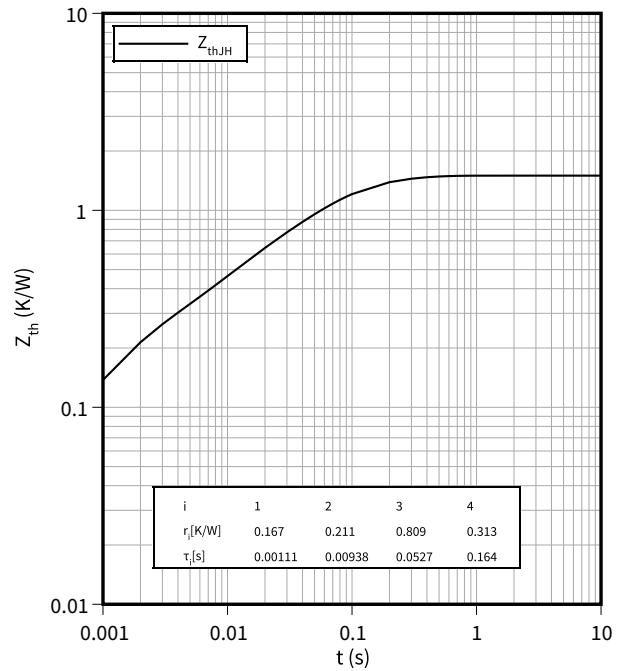
Forward characteristic (typical), Diode, Rectifier

$I_F = f(V_F)$



Transient thermal impedance, Diode, Rectifier

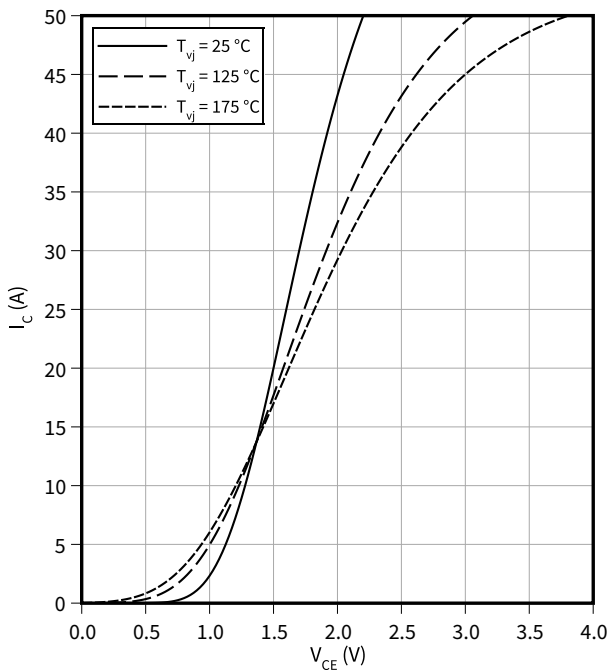
$Z_{th} = f(t)$



Output characteristic (typical), IGBT, Brake-Chopper

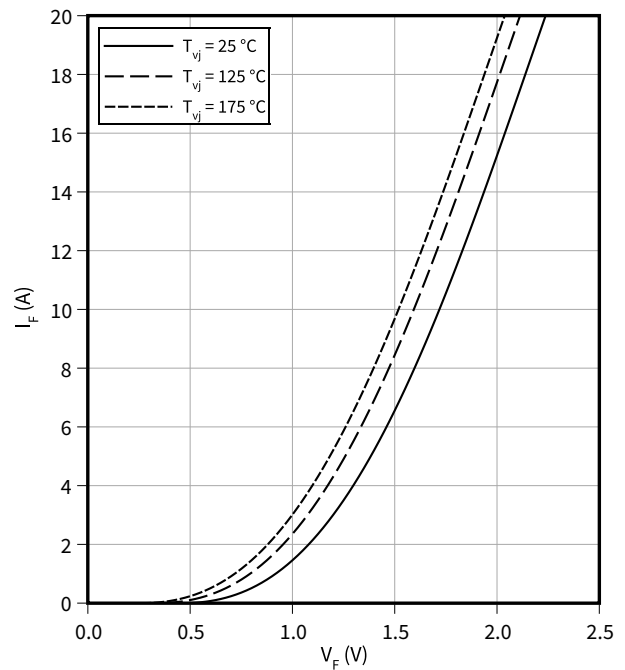
$I_C = f(V_{CE})$

$V_{GE} = 15 \text{ V}$



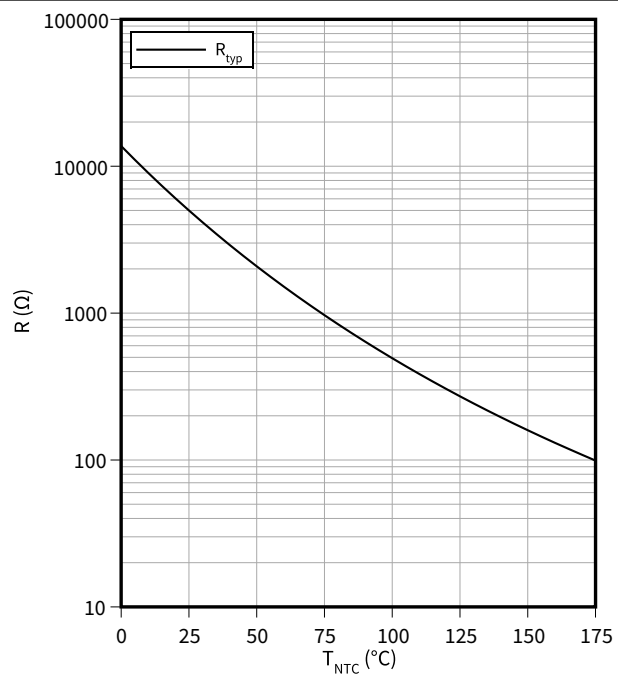
Forward characteristic (typical), Diode, Brake-Chopper

$I_F = f(V_F)$



Temperature characteristic (typical), NTC-Thermistor

$$R = f(T_{NTC})$$



9 Circuit diagram

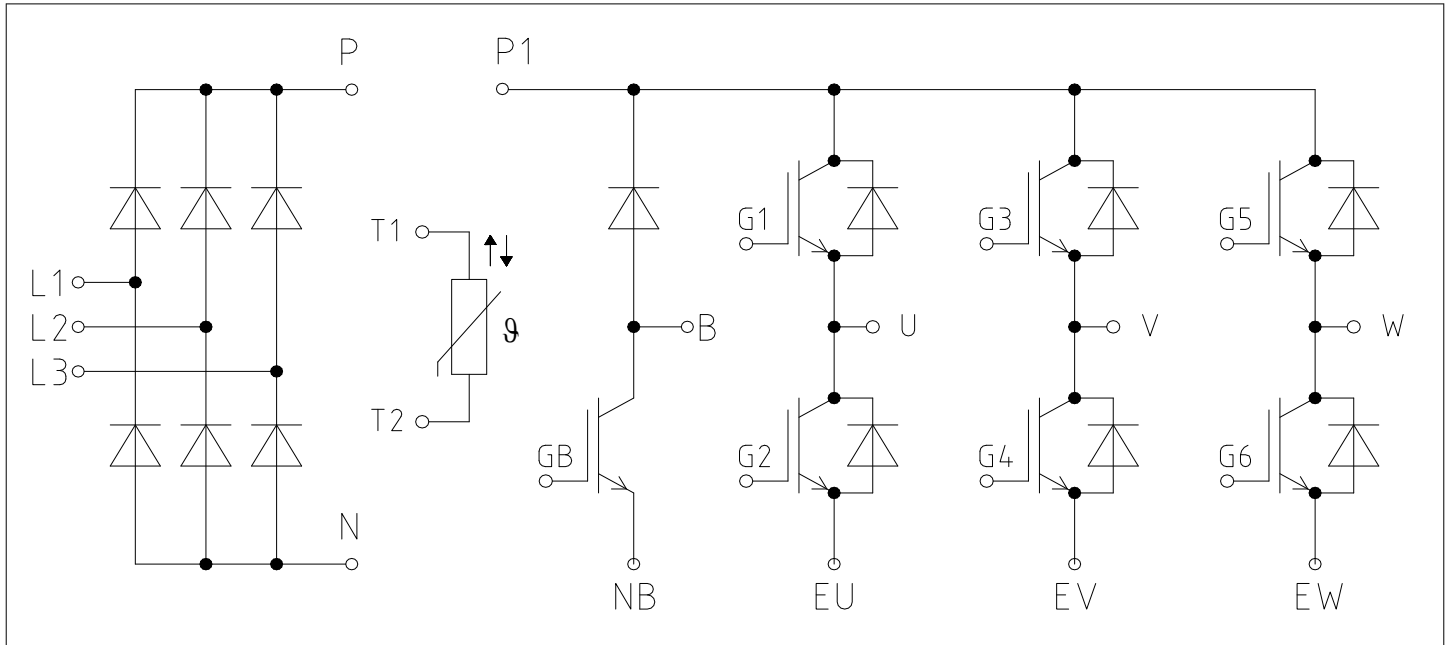


Figure 1

10 Package outlines

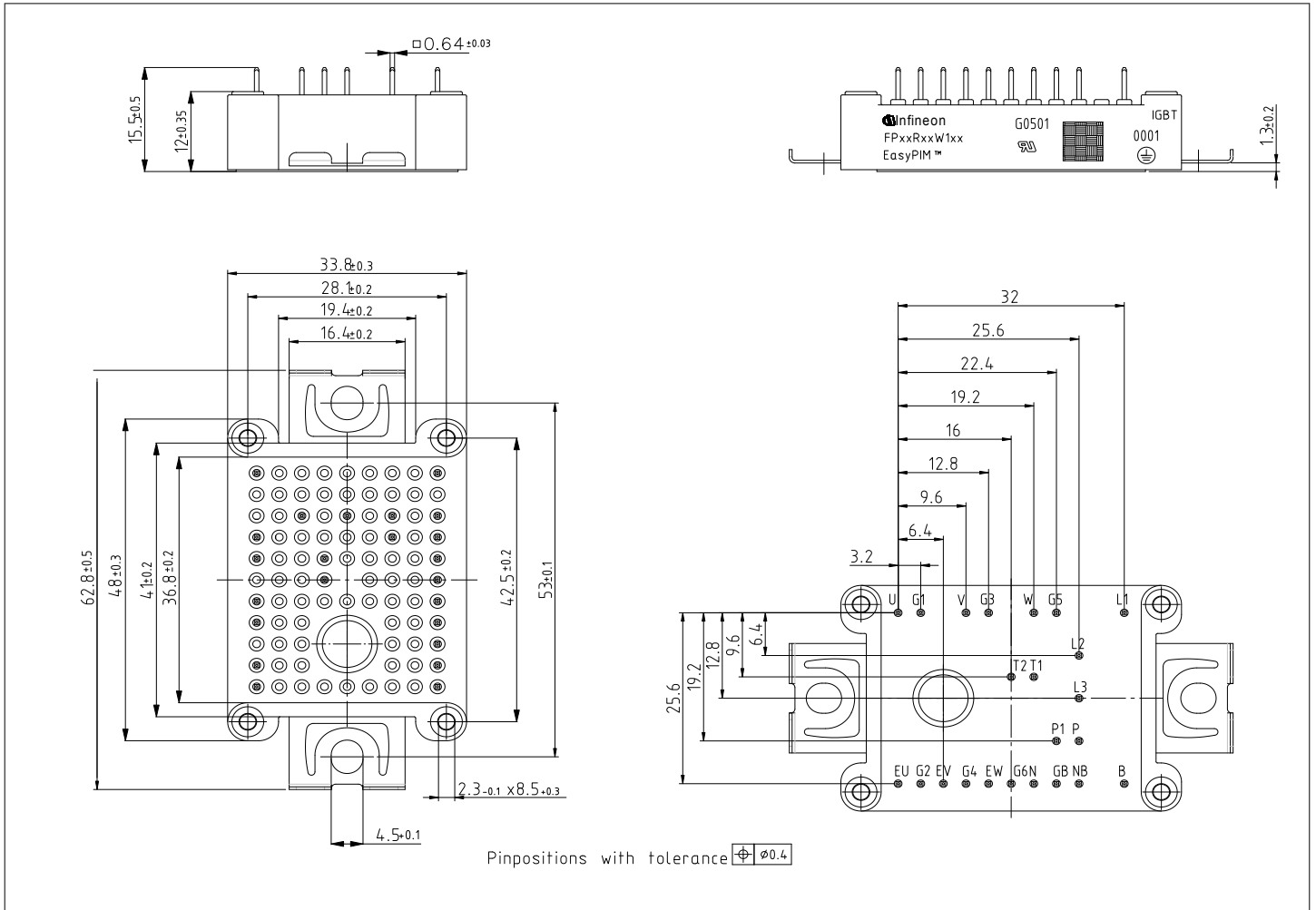


Figure 2

11 Module label code


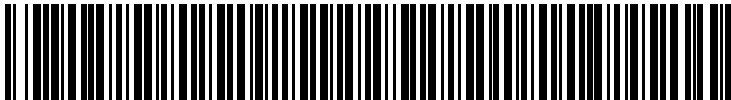
Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 - 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 - 21	15
	Date code (production week)	22 - 23	30
Example	 		
	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
V2.0	2019-08-12	Preliminary datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
0.10	2021-03-09	
1.00	2025-04-29	Final datasheet

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